

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	1	6297104.pn.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:43
2	BRS	L2	5	6840602.pn. or 6100243.pn.	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:46
3	BRS	L3	2984	(logic adj1 device) and (memory adj1 device)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:47
4	BRS	L4	44	first adj1 transistor near10 dielectric adj1 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:55
5	BRS	L5	4	3 and 4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:51

	Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS	16	49	(first adj1 transistor) near15 (dielectric adj1 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:56
7	BRS	17	4	3 and 6	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:56
8	BRS	18	5103	(transistor near15 (dielectric adj1 layer)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 22:36
9	BRS	L9	79	3 and 8	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:57
10	BRS	110	69	9 and thickness	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:57

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L11	37	10 and channel adj1 region	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:58
12	BRS	L12	13	11 and oxidation	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 21:58
13	BRS	L13	35	11 and oxid\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 22:15
14	BRS	L14	7000	transistor; pair15 (dielectric adj1 layer or silicon adj1 dioxide)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 22:46
15	BRS	L15	11	13 and 14	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 22:46

	Type	L #	Hits	Search Text	DBs	Time Stamp
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TI B	2002/03/28 22:47
16	BRS	L16	100	15 and channel	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:17
17	BRS	L17	89	16 and (source and drain)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:17
18	BRS	L18	407	3 and gate near1 oxide\$1	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TI B	2002/03/28 23:17
19	BRS	L19	389	18 and transistor	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:16
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TI B	2002/03/28 23:16

	Type	L #	Hits	Search Text	DBs	Time Stamp
21	BRS	L21	288	20 and channel	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:18
22	BRS	L22	258	21 and (source and drain)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:18
23	BRS	L23	129	22 and oxidation	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:18
24	BRS	L24	258	22 and oxid\$4	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:55
					USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B	2002/03/28 23:55

	Type	L #	Hits	Search Text	DBs	Time Stamp
					USPAT; US-PGP UB; EPO; JPO; 2002/03/29 DERWEN T; IBM_TD B	
27	RPS	L27	0	(silicon adj1 dioxide and silicon adj1 nitride) near10 (high adj1 oxidation)	USPAT; US-PGP UB; EPO; JPO; 2002/03/29 DERWEN T; IBM_TD B	00:47
28	RPS	L28	128	silicon adj1 dioxide near3 silicon adj1 nitride) near10 (oxidation)	USPAT; US-PGP UB; EPO; JPO; 2002/03/29 DERWEN T; IBM_TD B	00:49
29	RPS	L29	1	3 and 28	USPAT; US-PGP UB; EPO; JPO; 2002/03/29 DERWEN T; IBM_TD B	00:50
30	RPS	L30	91	28 and transistor	USPAT; US-PGP UB; EPO; JPO; 2002/03/29 DERWEN T; IBM_TD B	00:53

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	131	42	30 and high	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TD B	2002/03/29 00:54
2	BRS	132	42	31 and (memory and logic)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TD B	2002/03/29 00:54
3	BRS	132	42	31 and (memory or logic)	USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM TD B	2002/03/29 01:03